

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMJP.065AUS	APPLICATION NO. 09/779,397
		APPLICANT Michael A. Todd	
		FILING DATE February 7, 2001	GROUP 1762

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
1. <i>BL</i>	Varma, Ravi, "Organosilylation: Synthesis and Characterization of Silymethyl Methyl Ether," INORG. NUCL. CHEM. LETTERS, Vol. 6, pp. 9-14, 1970.

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EXAMINER [Signature] **DATE CONSIDERED** 12/12/02

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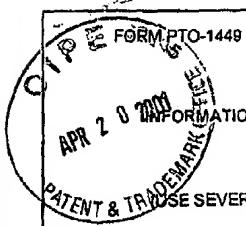
<p style="text-align: center;">U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p style="text-align: center;">(APR 2000) PATENT & TRADEMARK OFFICE USE SEVERAL SHEETS IF NECESSARY)</p>	ATTY. DOCKET NO. ASMJP.065AUS	APPLICATION NO. 09/779,397	
	APPLICANT Michael A. Todd	RECEIVED	
	FILING DATE February 7, 2001	APR 23 2001 GROUP Uukawa	1762

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
P	4,781,942	11/01/88	Leyden et al.			
	4,863,755	09/05/89	Hess et al.			
	4,894,352	01/16/90	Lane et al.			
	4,992,308	02/12/91	Hochberg et al.			
	5,011,706	04/30/91	Tarhay et al.			
	5,028,566	07/02/91	Legendijk			
	5,231,058	07/27/93	Maeda et al.			
	5,240,813	08/31/93	Watanabe et al.			
	5,314,724	05/24/94	Tsukune et al.			
	5,324,539	06/28/94	Maeda et al.			
	5,380,555	01/10/95	Mine et al.			
	5,433,788	07/18/95	Hu et al.			
	5,494,712	02/27/96	Hu et al.			
	5,554,570	09/10/96	Maeda et al.			
	5,563,105	10/06/96	Dobuzinsky et al.			
	5,703,404	12/30/97	Matsuura			
	5,840,821	11/24/98	Nakano et al.			
	5,876,798	03/02/99	Vassiliev			
	5,969,998	11/23/99	Sugahara et al.			
	5,998,522	12/07/99	Nakano et al.			
	6,045,877	04/04/00	Gleason et al.			
	6,051,321	04/18/00	Lee et al.			
	6,051,508	04/18/00	Takase et al.			
	6,054,379	04/25/00	Yau et al.			
	6,068,884	05/30/00	Rose et al.			

EXAMINER	DATE CONSIDERED
9/23/03	
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U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.
ASMJP.085AUS

APPLICATION NO.
09/779,397

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

PATENT & TRADEMARK
USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Michael A. Todd

FILING DATE
February 7, 2001

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
26.	WO 97/40207	10/30/97	PCT			X	
27.	WO 99/55526	11/04/99	PCT			X	
28.	EPO 367 004 B1	12/15/93	EPO			X	
29.	EP 0 436 185 B1	03/20/96	EPO			X	
30.	EP 0 723 600 B1	07/07/99	EPO			X	
31.	EP 0 771 886 A1	05/07/97	EPO			X	
32.	EP 0 935 283 A2	08/11/99	EPO			X	
33.	EP 0 960 958 A2	12/01/99	EPO			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	34. Bayer et al., Overall kinetics of SiOx remote-PECVD using different organosilicon monomers, Surface and Coatings Technology, 116-119 (1999) 874-878
	35. Berjoan et al., XPS and XPS valence band characterizations of amorphous or polymeric silicon based thin films prepared by PACVD from organosilicon monomers, J. Phys. IV France 9 (1999) pp. 1059-1068.
	36. Constant et al., Some Properties of amorphous SiXC1-x (H) alloys prepared by CVD from various organosilicon compounds, Solid State Chemistry, 1982, pp. 267-270
	37. Deville et al., An AES study of the influence of carbon on the chemical structure of some oxide films deposited by PECVD of organosilicon precursors, Applied Surface Science 137 (1999) 136-141
	38. Fonseca et al., Plasma Polymerization of Tetramethylsilane, Am. Chemical Society, 1993, 5, 1676-1682
	39. Inoue et al., Mass spectroscopy in plasma-enhanced chemical vapor deposition of silicon-oxide films using tetramethoxysilane, Thin Solid Films 316 (1998) 79-84
	40. Inoue et al., Spectroscopic studies on preparation of silicon oxide films by PECVD using organosilicon compounds, Plasma Sources Sci. Technol. 5 (1996) 339-343
	41. Loboda, M.J., New solutions for intermetal dielectrics using trimethylsilane-based PECVD processes, Microelectronic Engineering 50 (2000) 15-23
	42. Nguyen et al., Plasma organosilicon polymers, J. Electrochem. Soc., August 1985, pp. 1925-1932
	43. Shirafuji et al., PE-CVD of Fluorocarbon/SiO composite thin films using C4F8 and HMDSO1, Plasmas and Polymers, Vo. 4, No. 1, 1999, pp. 57-75
	44. Shirafuji et al., PE-CVD of fluorocarbon/silicon oxide composite thin films from TFE and HMDSO, Mat. Res. Soc. Symp. Proc. Vol. 544, pp. 173-178 1999
	45. Shirafuji et al., Plasma copolymerization of tetrafluoroethylene/hexamethyldisiloxane and In Situ Fourier Transform infrared spectroscopy of its gas phase, Jpn. J. Appl. Phys. Vol. 38 (1999) pp. 4520-4526
	46. Sugahara et al., Low Dielectric constant carbon containing SiO2 films deposited by PECVD technique using a novel CVD precursor, DUMIC Conference, Feb. 10-11, 1997, pp. 19-25
	47. Thomas et al., Plasma etching and surface analysis of a SiC:H films deposited by low temperature plasma enhanced chemical vapor deposition, Mat. Res. Soc. Symp. Proc. Vo. 334, 1994, pp. 445-450
	48. Matsuki, N., U.S. Patent Application No. 09/243,156 -Silicon-Polymer insulation film on semiconductor substrate and method for forming the film, filed February 2, 1999 NOT A PUBLICATION

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Michael A. Todd	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE February 7, 2001	GROUP 1762



EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
✓	1. Indrajit Banerjee, et al., "Characterization of Chemical Vapor Deposited Amorphous Fluorocarbons for Low Dielectric Constant Interlayer Dielectrics." J. Electrochem. Soc., Vol. 146(6), p. 2219 (1999).
	2. Sang-Soo Han, et al., "Deposition of Fluorinated Amorphous Carbon Thin Films as a Low-Dielectric Constant Material." J. Electrochem. Soc., Vol. 146(9), p.3383 (1999).
	3. H. Beckers, et al., "Synthesis and Properties of (Trifluoromethyl) trichlorosilane, a Versatile Precursor for CF ₃ Si Compounds," J. Organometal. Chem., Vol. 316, pp. 41-50, (1986).
	4. C.A. Costello and J.J. McCarthy, "Introduction of Organic Functional Groups onto the Surface of Poly(tetrafluoroethylene)," Proceedings of the ACS Division of Polymeric Materials Science and Engineering, Vol. 55 p. 893 (1986).
	5. K.G. Sharp and T.D. Coyle, "Synthesis and Some Properties of Trifluoro(trifluoromethyl) silane," J. Fluorine Chem., Vol. Q, pp. 249-251 (1971/72).
	6. Limb, Scott J., et al., "Growth of fluorcarbon polymer thin films with high CF ₂ fractions and low dangling bond concentrations by thermal chemical vapor deposition," App. Phys. Lett., Vol. 68(20), p. 2810 (1996).
	7. Washburne, Stephen S., et al. "Chloraminosilanes: I: The Preparation of Chloro(Dimethylamino) Hydrogen Silanes," Inorg. Nucl. Chem. Letters Vol. 5, pp. 17-19, Pergamon Press. 1969
	8. Savage, Charles R., et al., "Spectroscopic Characterization of Films Obtained in Pulsed Radio-Frequency Plasma Discharges of Fluorocarbon Monomers," Structure-Property Relations in Polymers, pp. 745-768, American Chemical Society, (1993).
	9. Sharp, K.G., et al., "Perfluoro(alkylsilanes). II: Trifluoro(trifluoromethyl) silane and Trifluoro(pentafluoroethyl) silane," Inorg. Chem., Vol. 11, No. 6, pp. 1259-1264, (1972). 1972
	10. Pam-Frost-Gorder, "Researchers Pioneer Techniques to Lubricate Microdevices," Research News, Ohio State University, http://www.acs.ohio-state.edu/units/research/ , (3/23/01). NOT A PUBLICATION

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FORM PTO-1449 <i>O I P E JC166</i> INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>SEP 25 2001</i> (USE SEVERAL SHEETS IF NECESSARY)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMJP.065AUS	APPLICATION NO. 09/779,397
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		FILING DATE February 7, 2001	GROUP 1762

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						YES	NO
<i>VJ</i>	WO 99/60621	11/25/1999	PCT				
<i>VJ</i>	WO 99/41423	08/19/1999	PCT				
<i>VJ</i>	WO 99/21706	05/06/1999	PCT				
<i>VJ</i>	WO 97/41592	11/06/1997	PCT				
<i>VJ</i>	EP 0 706 216 A2	04/10/1996	Europe				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>VJ</i>	A. PATENT ABSTRACTS OF JAPAN vol. 1998, no. 03, 27 February 1998 (1998-02-27) & JP 09 293716 A (KAWASAKI STEEL CORP), 11 November 1997 (1997-11-11) "abstract"
<i>VJ</i>	B. PATENT ABSTRACTS OF JAPAN vol. 1999, no.12, 29 October 1999 (1999-10-29) & JP 11 176829 A (INNOTECH CORP), 2 July 1999 (1999-07-02) "abstract"
<i>VJ</i>	C. Chandrasekhar et al., "New Silicon-Carbon Materials Incorporating Si ₄ C Building Blocks" Mat. Res. Soc. Symp. Proc. Vol. 441, Materials Research Society (1997)

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